PCN	Numbe	er:	20231	127	004	. 2	2			PCN Date: November 27, 202			
Title	:	Add Cu as Alte	rnative	Wire	Bas	se	Metal for Sel	ected Dev	ice	e(s))		
Cust	omer C	Contact:	Chang	е Ма	anag	je r	ment team	Dept:		Qu	ality Ser	vices	
Proposed 1 st Ship Date:					y 28	3, :	2024			requests Dec 28, 2023*			28, 2023*
*San	nple req	uests received a	after De	c 28	, 20	23	3 will not be s	upported.					
Char	nge Typ	e:											
	Assem	bly Site					Design				Wafer B	Bump	Material
\boxtimes	Assem	bly Process				Data Sheet					Wafer Bump P		Process
Assembly Materials					Part number			change			Wafer F	ab Si	te
☐ Mechanical Specification							Test Site				Wafer Fab Materials		
☐ Packing/Shipping/Labeling							Test Process				Wafer F	ab Pr	ocess
					F	P	CN Details						·
Dage		of Change											

Description of Change:

Texas Instruments is pleased to announce the qualification of new assembly material set to add Cu as an additional bond wire option for devices listed in "Product affected" section below. Devices will remain in current assembly facility and piece part changes as follows:

What	Current	Additional
Bond wire, Diameter	Die to LF: 0.96 mil Au/1mil Cu	Die to LF: 0.8 mil Cu
	Die to Die: 0.96 mil Au	Die to Die: 0.8 mil Cu

Reason for Change:

Continuity of supply.

- 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
- 2) Maximize flexibility within our Assembly/Test production sites.
- 3) Cu is easier to obtain and stock

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change ■ No Change ■ No Change No Change ■ No Change ■ No Change No Change	⊠ No Change	No Change	No Change ■ No Change ■ No Change No Change ■ No Change ■ No Change No Change

Changes to product identification resulting from this PCN:

None

Product Affected:

ISO1042BQDWQ1	UCC21710QDWQ1	UCC21737QDWRQ1	UCC21755QDWRQ1
ISO1042BQDWRQ1	UCC21710QDWRQ1	UCC21739QDWQ1	UCC21759QDWQ1
ISO1042QDWQ1	UCC21717QDWRQ1	UCC21739QDWRQ1	UCC21759QDWRQ1
ISO1042QDWRQ1	UCC21732QDWQ1	UCC21750QDWQ1	
SN21750QDWRQ1	UCC21732QDWRQ1	UCC21750QDWRQ1	

Qualification Report Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 19-October-2023

Product Attributes

Adulthouse	Qual Device:	Qual Device:	QBS Process Reference:	QBS Process Reference:	QBS Product Reference:	
Attributes	ISO6763QDWRQ1	UCC21540QDWKRQ1	<u>UCC23513QDWYQ1</u>	IS07741FQDWQ1	<u>ISO6763QDWRQ1</u>	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	
Product Function	Interface	Power Management	Power Management	Interface	Interface	
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8, MH8	RFAB, RFAB	MH8, MH8	RFAB, RFAB	
Assembly Site	MLA	TAI	TAI	TAI	MLA	
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	
Package Designator	DW	DWK	DWY	DW	DW	
Pin Count	16	14	6	16	16	

QBS: Qual By Similarity

Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C Qual Device UCC21540QDWKRQ1 is qualified at MSL3 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

				alu L	olopiay ca i	as. Haiiii	001 01	ioto / Total	Sample Size	Total lanca		
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Process Reference: ISO7741FQDWQ1	QBS Product Reference: ISO6763QDWRQ
Test Group	A - Acc	elerated Enviror	ment St	ress Tes	sts							
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	No Fails	No Fails	-	-	No Fails
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	3/231/0	-	-	1/77/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	3/231/0	-	-	1/77/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	-	-	1/77/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	1/5/0	-	-	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	3/135/0	-	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	-	1/45/0
Test Group	B - Acc	elerated Lifetime	Simula	tion Tes	ts							
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours		-	3/231/0	3/231/0	-
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	3/2400/0	-
Test Group	C - Paci	kage Assembly	Integrity	Tests	'	'						'
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0	3/90/0	-
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Process Reference: ISO7741FQDWQ1	QBS Product Reference: ISO6763QDWRQ1
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67		-	-	3/30/0	-	-
Test Group	D - Die F	abrication Relia	ability Te	sts								
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verificatio	n Tests									
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	Device specific data [1]	-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	1500 Volts	Device specific data [1]	Device specific data [1]	-	-	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	Device specific data [1]	-	-	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	3/90/0	3/90/0	

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

 ${\sf Room/Hot: THB\,/\,HAST,\,TC\,/\,PTC,\,HTSL,\,ELFR,\,ESD\,\&\,LU}$

Room: AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

Qualification Report Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Approve Date 28-April-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

			. <u></u>	,		1 10t3 / 10tai 3aii	.p.o oo	,	
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: AMC1305M25QDWQ1	Qual Device: AMC1305M25QDWQ1
Test Gr	oup A - A	Accelerated Environme	ent Stres	s Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	No Fails	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	3/231/0	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	-
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	-
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	-
TC	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	3/210/0
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0

A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	3/135/0
A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-
A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	2000 Hours	3/132/0	3/132/0
A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	3/3/0
oup B - A	Accelerated Lifetime Si	mulation	Tests					
oup C - F	Package Assembly Inte	grity Tes	sts					
C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-
С3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-
C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-
oup D - E	Die Fabrication Reliabili	ty Tests						
D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
D5		_		Stress Migration	-	-	Completed Per Process Technology	Completed Per Process Technology
	A4.2.3 A4.2.4 A4.2.5 A6.1 A6.1.1 A6.2 A6.2.1 coup C - F C1 C2 C3 C4 cup D - C D1 D2 D3	A4.2.3 - A4.2.4 - A4.2.5 - A6.1 JEDEC JESD22- A103 A6.1.1 - A6.2 JEDEC JESD22- A103 A6.2.1 - Oup B - Accelerated Lifetime Si Oup C - Package Assembly Inte C1 AEC Q100-001 C2 MIL-STD883 Method 2011 C3 JEDEC J-STD-002 C4 JEDEC J-STD-002 C4 JEDEC J-STD-002 C4 JEDEC J-STD-002 D1 JESD61 D2 JESD35 D3 JESD60 & 28 D4 -	A4.2.3 - 3 A4.2.4 - 3 A4.2.5 - 3 A6.1 JEDEC JESD22- 3 A6.1.1 - 3 A6.2 JEDEC JESD22- 3 A6.2.1 - 3 Oup B - Accelerated Lifetime Simulation oup C - Package Assembly Integrity Test C1 AEC Q100-001 1 C2 MIL-STD883 Method 1 C3 JEDEC J-STD-002 1 C4 JEDEC J-STD-002 1 C4 JEDEC JESD22- 1 Oup D - Die Fabrication Reliability Tests D1 JESD61 - D2 JESD35 - D3 JESD60 & 28 - D4	A4.2.3 - 3 30 A4.2.4 - 3 3 30 A4.2.5 - 3 3 30 A6.1 JEDEC JESD22- 3 45 A6.1.1 - 3 1 A6.2 JEDEC JESD22- 3 45 A6.2.1 - 3 1 Oup B - Accelerated Lifetime Simulation Tests Oup C - Package Assembly Integrity Tests C1 AEC Q100-001 1 30 C2 MIL-STD883 Method 1 30 C3 JEDEC J-STD-002 1 15 C3 JEDEC J-STD-002 1 15 C4 JEDEC JESD22- 1 10 oup D - Die Fabrication Reliability Tests D1 JESD61 D2 JESD35 D3 JESD60 & 28	A4.2.2 - 3 1 TC, 2X A4.2.3 - 3 3 30 Wire Bond Shear, post TC, 2X A4.2.4 - 3 3 30 Bond Pull over Stitch, post TC, 2X A4.2.5 - 3 3 30 Bond Pull over Ball, post TC, 2X A6.1 JEDEC JESD22- 3 45 High Temperature Storage Life A6.1.1 - 3 1 Cross Section, post HTSL, 1X A6.2 JEDEC JESD22- 3 45 High Temperature Storage Life A6.1 - 3 1 Cross Section, post HTSL, 1X A6.2.1 - 3 1 Cross Section, post HTSL, 2X OUP B - Accelerated Lifetime Simulation Tests OUP C - Package Assembly Integrity Tests C1 AEC Q100-001 1 30 Wire Bond Shear C2 MIL-STD883 Method 2011 25 PB Solderability C3 JEDEC J-STD-002 1 15 PB Solderability C3 JEDEC J-STD-002 1 15 PB-Free Solderability C4 JEDEC JESD22- 1 10 Physical Dimensions OUP D - Die Fabrication Reliability Tests D1 JESD61 - Electromigration D2 JESD35 - Hot Carrier Injection D4 Negative Bias Temperature Instability	A4.2.2 - 3 1 TC, 2X section A4.2.3 - 3 3 30 Wire Bond Shear, post stress A4.2.4 - 3 3 30 Bond Pull over Ball, post TC, 2X A4.2.5 - 3 3 30 Bond Pull over Ball, post TC, 2X A6.1 JEDEC JESD22- 3 45 High Temperature Storage Life 150C A6.1.1 - 3 1 Cross Section, post High Temperature Storage Life 150C A6.2 JEDEC JESD22- 3 45 High Temperature Storage Life 150C A6.2.1 - 3 1 Cross Section, post HTSL, 1X Post stress cross section A6.2.1 - 3 1 Cross Section, post HTSL, 2X Post stress cross section A6.2.1 - 3 1 Wire Bond Shear Minimum of 5 devices, 30 wires Cpk>1.67 C2 MIL-STD883 Method 1 30 Wire Bond Shear Minimum of 5 devices, 30 wires Cpk>1.67 C3 JEDEC J-STD-002 1 15 PB Solderability P5% Lead Coverage 2011 Physical Diagnosis Cpk>1.67 C4 JEDEC J-STD-002 1 15 PB-Free Solderability P5% Lead Coverage Physical Diagnosis Cpk>1.67 C4 JEDEC J-STD-002 1 10 Physical Diagnosis Cpk>1.67 C5 JEDEC J-STD-002 1 Time Dependent Diagnosis Cpk>1.67 C6 JEDEC J-STD-002 1 Time Dependent Diagnosis Cpk>1.67 C7 JEDEC J-STD-002 1 Time Dependent Diagnosis Cpk>1.67 C8 JEDEC J-STD-002 1 Time Dependent Diagnosis Cpk>1.67 C9 JESD61 - Electromigration - Time Dependent Diagnosis Cpk>1.67 C9 JESD61 - Not Carrier Injection - Negative Bias Temperature Instability Instability Temperature Instability Temperat	A4.2.2 - 3 1 TC, 2X section Completed A4.2.3 - 3 3 30 Wire Bond Shear, post TC, 2X A4.2.4 - 3 3 30 Bond Pull over Sitch, post TC, 2X A4.2.5 - 3 3 30 Bond Pull over Ball, post TC, 2X A6.1 JEDEC JESD22- 3 45 High Temperature Storage Life 150C Hours A6.1.1 - 3 1 Cross Section, post HTSL, 1X A6.2 JEDEC JESD22- 3 45 High Temperature Storage Life 150C Hours A6.2.1 - 3 1 Cross Section, post HTSL, 1X A6.2.1 - 3 1 Cross Section, post HTSL, 1X A6.2.1 - 3 1 Cross Section, post HTSL, 2X A6.2.1 - 3 1 Cross Section, post HTSL, 2X COMPleted Storage Life 150C Hours COMPLETE STORAGE Assembly Integrity Tests COUP C - Package Assembly Integrity Tests C1 AEC Q100-001 1 30 Wire Bond Shear Minimum of 5 devices, 30 wires Cpk-1.67 C2 MIL-STD883 Method 1 30 Wire Bond Pull Minimum of 5 devices, 30 wires Cpk-1.67 C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - C4 JEDEC JESD22- 1 10 Physical Dimensions Cpk-1.67 C0 JEDEC JESD22- 1 Told Physical Dimensions Cpk-1.67 C0 JEDEC JESD22- 1 Time Dependent Dielectric Breakdown D1 JESD61 Electromigration	A4.2.2 - 3 1 TC, 2X section Completed 3/30 A4.2.3 - 3 3 30 Wire Bond Shear, post TC, 2X Post stress Wires 3/9/0 A4.2.4 - 3 3 30 Bond Pull over Salth, post TC, 2X Post stress Wires 3/9/0 A4.2.5 - 3 3 30 Bond Pull over Ball, post TC, 2X Post stress Wires 3/9/0 A6.1 JEDEC JESD22- 3 45 High Temperature Storage Life

QBS: Qual By Similarity

Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C

Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

ZVEI ID reference: SEM-PA-08

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disdaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.